

2MBI300VD-120-50

IGBT Modules

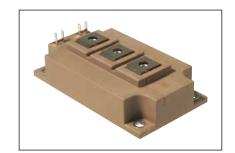
IGBT MODULE (V series) 1200V / 300A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

■ Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
Collector-Emit	ter voltage	Vces			1200		
Gate-Emitter voltage		V _{GES}			±20	V	
5		lo.	Continuous	Tc=100°C	300		
Collector current		Ic	Continuous	Tc=25°C	360		
		Ic pulse	1ms	·	600		
		-lc					
		-lc pulse	1ms	1ms			
Collector power dissipation		Pc	1 device	1 device		W	
Junction temperature		Tj			175	°C	
Operating junction temperature (under switching conditions)		T _{jop}		·	150		
Case temperature		Tc			125		
Storage temperature		Tstg					
Isolation voltage	between terminal and copper base (*1)	Viso	AC: 1min.	AC : 1min.		VAC	
Screw torque	Mounting (*2)				6.0	N m	
	Terminals (*3)]-			5.0	IN III	

Note *1: All terminals should be connected together during the test. Note *2: Recommendable Value : 3.0-6.0 Nm (M5 or M6) Note *3: Recommendable Value : 2.5-5.0 Nm (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

ems	Cumbala	nbols Conditions		Characteristics		Heite		
ems	Symbols			min.	typ.	max.	Units	
Zero gate voltage collector current	gate voltage collector current Ices VGE = 0V, VGE = 1200V			-	-	2.0	mA	
Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	400	nA	
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 300mA		6.0	6.5	7.0	V	
	V _{CE (sat)} (terminal)	V _{GE} = 15V I _C = 300A	Tj=25°C	-	2.00	2.45	V	
			Tj=125°C	-	2.35	-		
Collector-Emitter saturation voltage			Tj=150°C	-	2.40	-		
Conector-Emitter Saturation voltage	V _{CE (sat)} (chip)		Tj=25°C	-	1.85	2.10		
			Tj=125°C	-	2.15	-		
			Tj=150°C	-	2.20	-		
Internal gate resistance	R _{g(int)}	-		-	2.5	-	Ω	
Input capacitance Turn-on time	Cies	$V_{CE} = 10V, V_{GE} = 0V, f = 1MHz$		-	24.0	-	nF	
i	ton			-	0.60	-		
Turn-on time	tr	V _{CC} = 600V, I _C = 300A V _{GE} = ±15V, R _G = 1.8Ω Tj = 150°C, Ls =30nH		-	0.20	-	μsec	
	tr (i)			-	0.05	-		
Turn-off time	toff			-	0.80	-		
Turn-on time	tf			-	0.08	-		
	VF	V _{GE} = 0V I _F = 300A	Tj=25°C	-	1.85	2.25	V	
	(terminal)		Tj=125°C	-	2.00	-		
Forward on voltage	(terrillial)		Tj=150°C	-	1.95	-		
Forward on voitage	V _F (chip)		Tj=25°C	-	1.70	1.95		
			Tj=125°C	-	1.85	-		
			Tj=150°C	-	1.80	-		
Reverse recovery time	trr	I _F = 300A		-	0.15	-	usec	

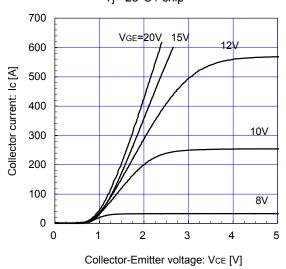
Thermal resistance characteristics

	Symbols		Characteristics			
Items		Conditions	min.	typ.	max.	Units
Thermal resistance (Adenies)	Dth/; a)	IGBT	-	-	0.068	°C/W
Thermal resistance (1device)	Rth(j-c)	FWD	-	-	0.110	
Contact thermal resistance (1device) (*4)	Rth(c-f)	with Thermal Compound	-	0.0125	-	

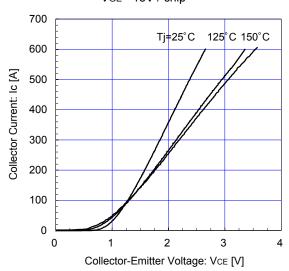
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

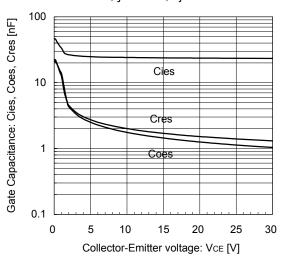
Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



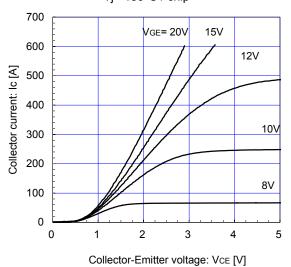
Collector current vs. Collector-Emitter voltage (typ.) VGE= 15V / chip



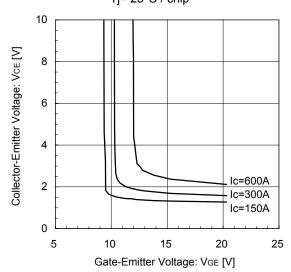
Gate Capacitance vs. Collector-Emitter Voltage VGE= 0V, f= 1MHz, Tj= 25°C



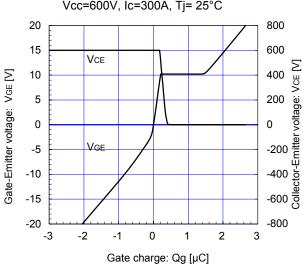
Collector current vs. Collector-Emitter voltage (typ.) Tj= 150°C / chip

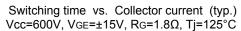


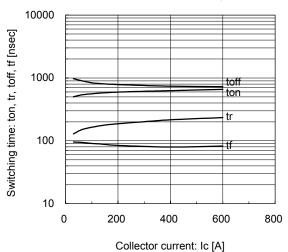
Collector-Emitter voltage vs. Gate-Emitter voltage Tj= 25°C / chip



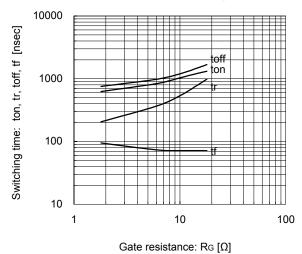
Dynamic Gate Charge (typ.) Vcc=600V, Ic=300A, Tj= 25°C



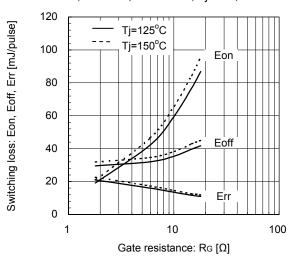




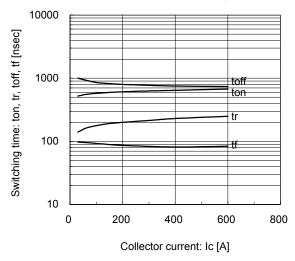
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=300A, VgE=±15V, Tj=125°C



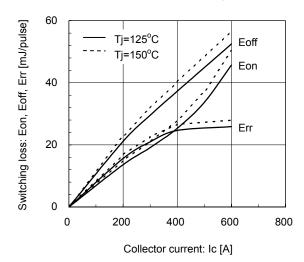
Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=300A, VgE=±15V, Tj=125, 150°C



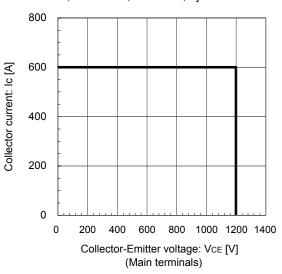
Switching time vs. Collector current (typ.) Vcc=600V, $VgE=\pm15V$, $Rg=1.8\Omega$, $Tj=150^{\circ}C$



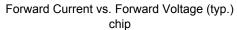
Switching loss vs. Collector current (typ.) Vcc=600V, $VgE=\pm15V$, $Rg=1.8\Omega$, Tj=125, $150^{\circ}C$

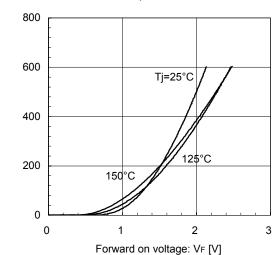


Reverse bias safe operating area (max.) +VGE=15V, -VGE=15V, $RG=1.8\Omega$, $Tj=150^{\circ}C$

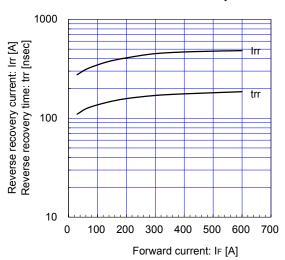


Forward current: IF [A]

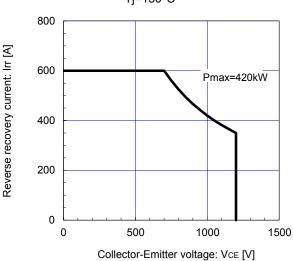




Reverse Recovery Characteristics (typ.) Vcc=600V, $VgE=\pm15V$, $Rg=1.8\Omega$, $Tj=150^{\circ}C$

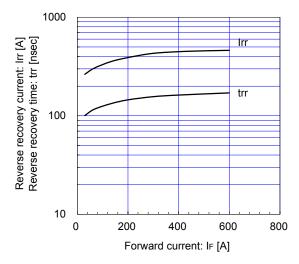


FWD safe operating area (max.) Tj=150°C

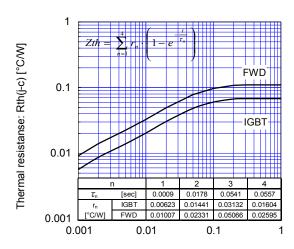


(Main terminals)

Reverse Recovery Characteristics (typ.) Vcc=600V, $VgE=\pm15V$, $Rg=1.8\Omega$, $Tj=125^{\circ}C$



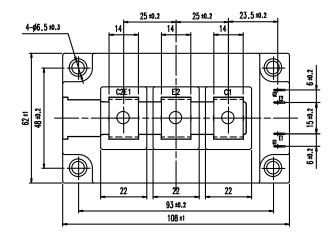
Transient Thermal Resistance (max.)

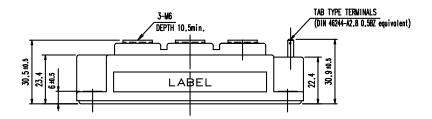


Pulse Width: Pw [sec]

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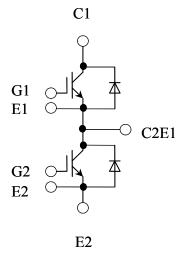
■ Outline Drawings (Unit: mm)





Weight: 370g (typ.)

■ Equivalent Circuit



http://www.fujielectric.com/products/semiconductor/

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- Measurement equipment

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- Audiovisual equipment
- Electrical home appliances Personal equ
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